

PNP medium power transistor

Datasheet - production data

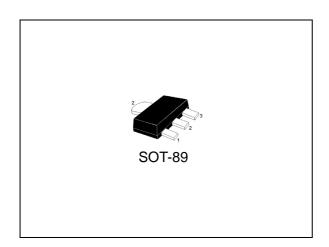
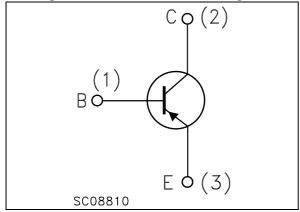


Figure 1. Internal schematic diagram



Features

- In compliance with the 2002/93/EC European directive
- · Available in tape & reel packing
- Surface mounting devices in medium power SOT-223 and SOT-89 packages

Applications

- Voltage regulation
- Relay driver
- Generic switch

Description

The STF826 is a PNP transistor manufactured using planar Technology resulting in rugged high performance devices.

Table 1. Device summary

Order code	Marking	Package	Packaging
STF826	826	SOT-89	Tape and reel

Contents STF826

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1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-60	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-30	V
V _{EBO}	Collector-base voltage (I _C = 0)	-5	V
I _C	Collector current	-3	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-6	Α
I _B	Base current	-1	Α
I _{BM}	Base peak current (t _P < 5 ms)	-2	А
P _{TOT}	Total dissipation at T _c = 25 °C	1.4	W
T _{STG}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb} ⁽¹⁾	Thermal Resistance Junction-Amb max.	89	°C/W

^{1.} Device mounted on a PCB area of 1 cm².

Electrical characteristics STF826

2 Electrical characteristics

(T_{CASE} = 25 °C; unless otherwise specified)

Table 4. Electrical characteristics

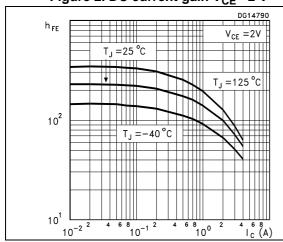
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = -60 V			-10	μΑ
I _{CEO}	Collector cut-off current (I _B = 0)	V _{CE} = -30 V			-100	μА
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -5 V			-10	μА
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA	-60			V
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -10 mA	-30			V
V _{(BR)EBO}	Collector-emitter breakdown voltage (I _C = 0)	I _E = -100 μA	-5			V
		$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$			-0.4	V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = -2 \text{ A}, I_B = -100 \text{ mA}$			-0.7	V
		$I_C = -3 \text{ A}, I_B = -150 \text{ mA}$			-1.1	V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	$I_C = -2 \text{ A}, I_B = -100 \text{ mA}$			-1.2	V
		$I_C = -100 \text{ mA}, V_{CE} = -2 \text{ V}$	100			
h _{FE}	DC current gain	I _C = -1 A, V _{CE} = -2 V	80		300	
		$I_C = -3 \text{ A}, V_{CE} = -2 \text{ V}$	30			
f _T	Transistor frequency	$V_{CE} = -10 \text{ V}, I_{c} = -0.1 \text{ A}$		100		MHz

^{1.} Pulsed duration = 300 ms, duty cycle \leq 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. DC current gain V_{CE}= 2 V

Figure 3. DC current gain V_{CE}= 5 V



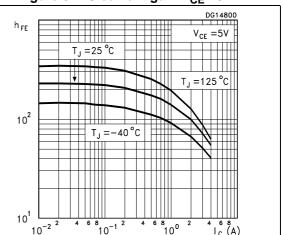
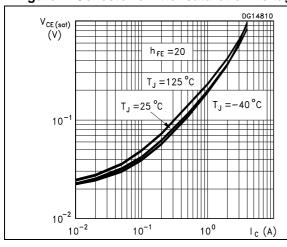


Figure 4. Collector-emitter saturation voltage

Figure 5. Base-emitter saturation voltage



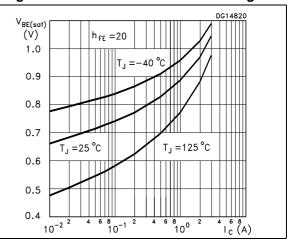
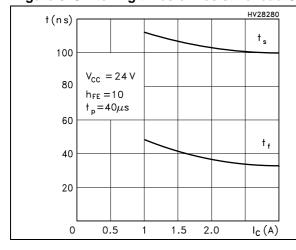
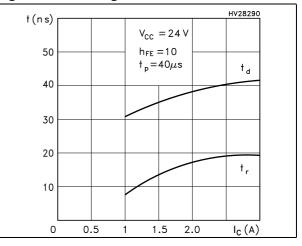


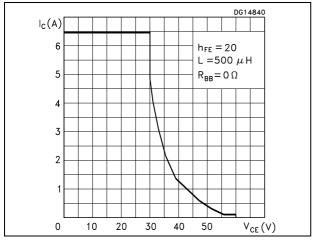
Figure 6. Switching times on resistive load OFF Figure 7. Switching times resistive on load ON





Electrical characteristics STF826

Figure 8. Reverse biased area



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3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 5. SOT-89 mechanical data

Dim.		mm	
	Min.	Тур.	Max.
А	1.40		1.60
В	0.44		0.56
B1	0.36		0.48
С	0.35		0.44
C1	0.35		0.44
D	4.40		4.60
D1	1.62		1.83
D3		0.90	
E	2.29		2.60
е	1.42		1.57
e1	2.92		3.07
Н	3.94		4.25
H1	2.70		3.10
К	1°		8°
L	0.89		1.20
R		0.25	
β		90°	



<u>D3</u> BOTTOM VIEW SIDE VIEW <u>C1</u> <u>D1</u> <u>C</u> B1(x2) D TOP VIEW 7098166_REV_E

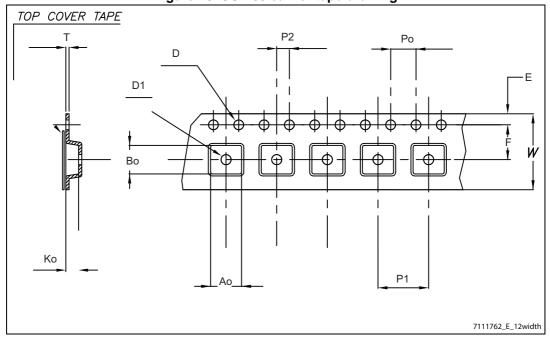
Figure 9. SOT-89 drawings

4 Packaging mechanical data

Table 6. SOT-89 carrier tape dimensions

Dim.	n	nm.
Diiii.	Values	Tolerance
Ao	4.91	± 0.10
Во	4.52	± 0.10
Ко	1.90	± 0.10
F	5.50	± 0.10
E	1.75	± 0.10
W	12	± 0.30
P2	2	± 0.10
Po	4	± 0.10
P1	8	± 0.10
Т	0.30	± 0.10
D	Ø 1.55	± 0.05
D1	Ø 1.60	± 0.10

Figure 10. SOT-89 carrier tape drawing



PIN 1: BASE
PIN 2: COLLECTOR
PIN 3: EMITTER

SOT-89 top view

Figure 11. SOT-89 package orientation in carrier tape

STF826 Revision history

5 Revision history

Table 7. Document revision history

Date	Revision	Changes
03-Aug-2005	1	Initial release.
25-Feb-2013	2	Removed part number STN826 in SOT-223 package.

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12/12 DocID11748 Rev 2

